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(54) REDISTRIBUTION SUBSTRATE, SEMICONDUCTOR PACKAGE INCLUDING THE SAME, AND METHOD OF FABRICATING REDISTRIBUTION **SUBSTRATE**

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ABSTRACT (57)

A redistribution substrate includes first and second insulating layers; a wiring layer, and a metal layer. The wiring pattern includes a via portion penetrating the first insulating layer and a pad portion on the via portion, the pad portion extending onto an upper surface of the first insulating layer. The metal layer covers an upper surface of the wiring pattern. The second insulating layer is provided on the first insulating layer and covers the pad portion and the metal layer. The wiring pattern includes a first metal. The metal layer includes the first metal and a second metal. The metal layer includes a first portion vertically overlapping the pad portion, and a second portion surrounding the first portion, and a concentration of the first metal in the first portion of the metal layer is greater than a concentration of the first metal in the second portion of the metal layer.

